

RoHS Compliant Product
A suffix of "-C" specifies halogen and lead-free

DESCRIPTION

These miniature surface mount MOSFETs utilize a high cell density process. Low $R_{DS(on)}$ assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are PWMDC-DC converters, power management in portable and battery-powered products such as computers, printers, battery charger, telecommunication power system, and telephones power system.

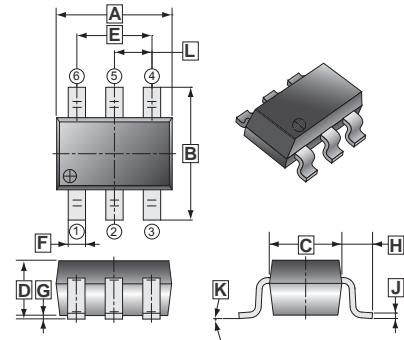
FEATURES

- Low $R_{DS(on)}$ provides higher efficiency and extends battery life.
- Miniature TSOP-6 surface mount package saves board space.
- High power and current handling capability.

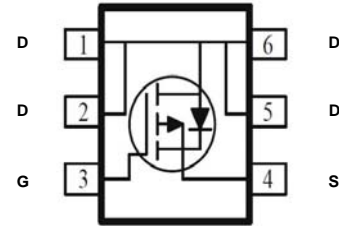
PACKAGE INFORMATION

Package	MPQ	LeaderSize
TSOP-6	3K	7' inch

TSOP-6



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	0	0.10
B	2.60	3.00	H	0.60	REF.
C	1.40	1.80	J	0.12	REF.
D	1.10	MAX.	K	0°	10°
E	1.90	REF.	L	0.95	REF.
F	0.30	0.50			



ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current ¹	I_D	$T_A=25^\circ\text{C}$	-4.9
		$T_A=70^\circ\text{C}$	-4.0
Pulsed Drain Current ²	I_{DM}	-20	A
Continuous Source Current (Diode Conduction) ¹	I_S	-1.7	A
Power Dissipation ¹	P_D	$T_A=25^\circ\text{C}$	2
		$T_A=70^\circ\text{C}$	1.3
Operating Junction and Storage Temperature Range	T_j, T_{stg}	-55 ~ 150	$^\circ\text{C}$
Thermal Resistance Ratings			
Maximum Junction to Ambient ¹	$t \leq 5 \text{ sec}$	$R_{\theta JA}$	62.5
			110
			$^\circ\text{C} / \text{W}$

Notes:

1. Surface Mounted on 1" x 1" FR4 Board.
2. Pulse width limited by maximum junction temperature.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static						
Gate-Threshold Voltage	$V_{GS(th)}$	-0.7	-	-	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
Gate-Body Leakage	I_{GSS}	-	-	± 100	nA	$V_{DS} = 0\text{V}, V_{GS} = \pm 12\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}	-	-	-1	μA	$V_{DS} = -16\text{V}, V_{GS} = 0\text{V}$
		-	-	-5		$V_{DS} = -16\text{V}, V_{GS} = 0\text{V}, T_J = 55^\circ\text{C}$
On-State Drain Current ¹	$I_{D(on)}$	-15	-	-	A	$V_{DS} = -4.5\text{V}, V_{GS} = -4.5\text{V}$
Drain-Source On-Resistance ¹	$R_{DS(ON)}$	-	-	56	m Ω	$V_{GS} = -4.5\text{V}, I_D = -4.9\text{A}$
		-	-	80		$V_{GS} = -2.5\text{V}, I_D = -4.2\text{A}$
		-	-	150		$V_{GS} = -1.8\text{V}, I_D = -3.1\text{A}$
Forward Transconductance ¹	g_{fs}	-	11	-	S	$V_{DS} = -10\text{V}, I_D = -4.9\text{A}$
Diode Forward Voltage	V_{SD}	-	-0.8	-	V	$I_S = 1.7\text{A}, V_{GS} = 0\text{V}$
Dynamic ²						
Total Gate Charge	Q_g	-	8	-	nC	$V_{DS} = -10\text{V}, V_{GS} = -4.5\text{V}, I_D = -4.9\text{A}$
Gate-Source Charge	Q_{gs}	-	1.8	-		
Gate-Drain Charge	Q_{gd}	-	1.9	-		
Turn-on Delay Time	$T_{d(on)}$	-	22	-	nS	$V_{DD} = -10\text{V}, V_{GEN} = -4.5\text{V}, R_L = 6\Omega, I_D = -1\text{A}$
Rise Time	T_r	-	35	-		
Turn-off Delay Time	$T_{d(off)}$	-	45	-		
Fall Time	T_f	-	25	-		

Notes:

1. Pulse test : $PW \leq 300 \mu\text{s}$ duty cycle $\leq 2\%$.
2. Guaranteed by design, not subject to production testing.

CHARACTERISTICS CURVE

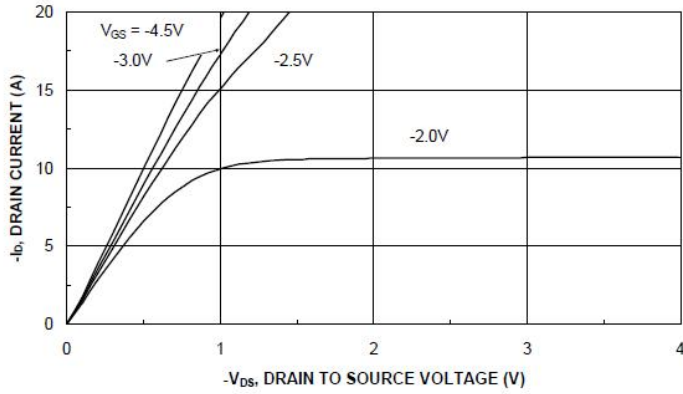


Figure 1. Output Characteristics

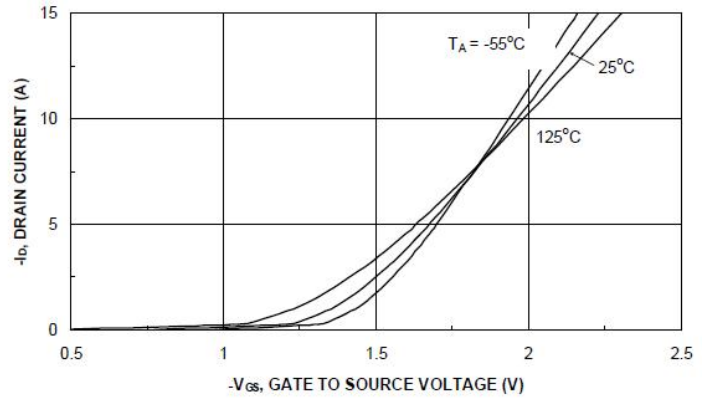


Figure 2. Transfer Characteristics

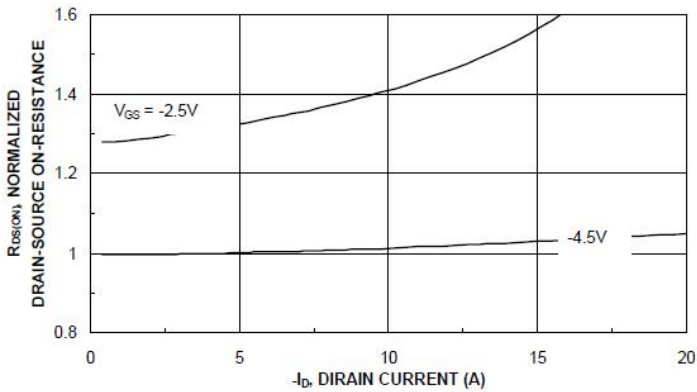


Figure 3. On-Resistance vs. Drain Current

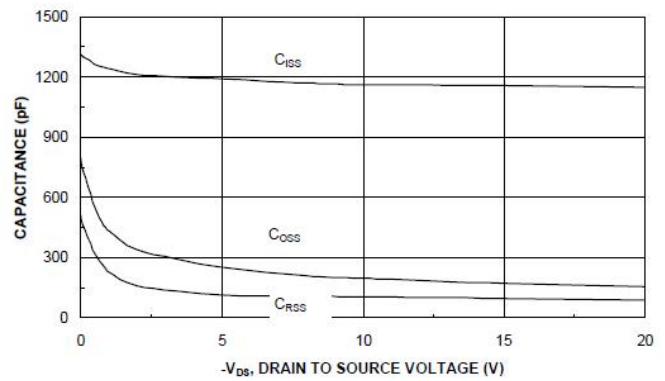


Figure 4. Capacitance

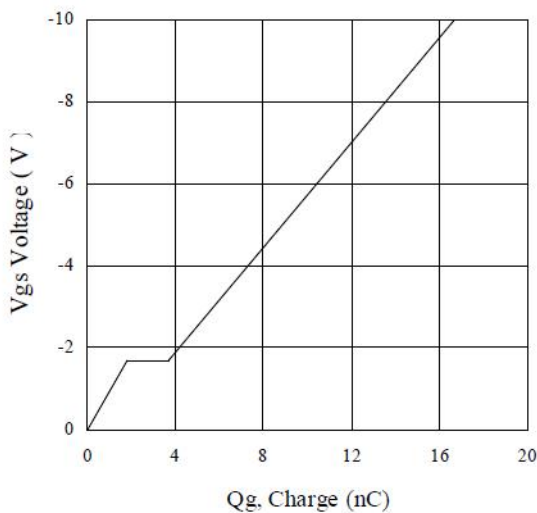


Figure 5. Gate Charge

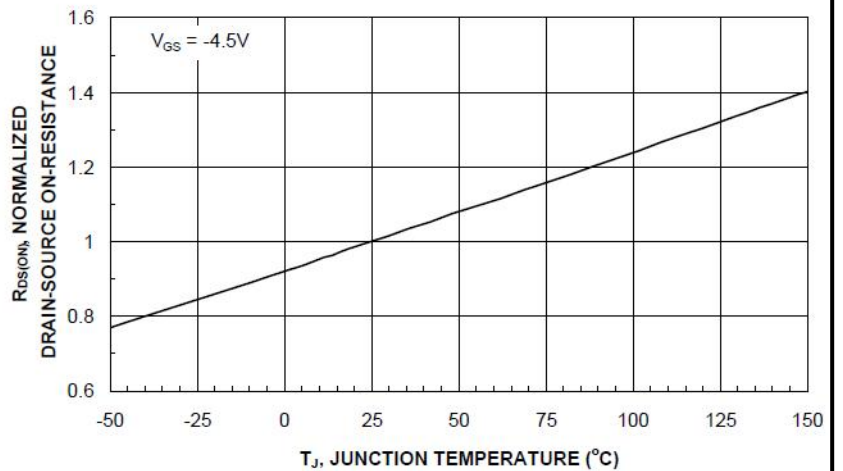


Figure 6. On-Resistance vs. Junction Temperature

CHARACTERISTICS CURVE

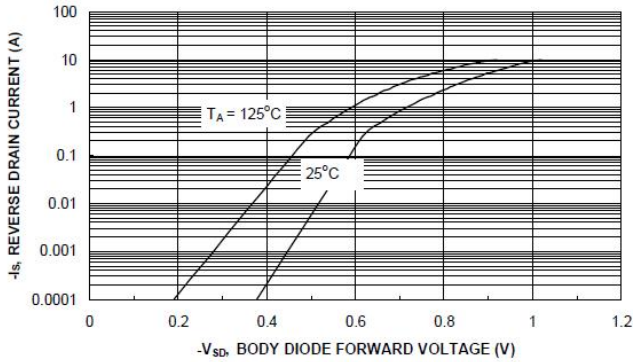


Figure 7. Source-Drain Diode Forward Voltage

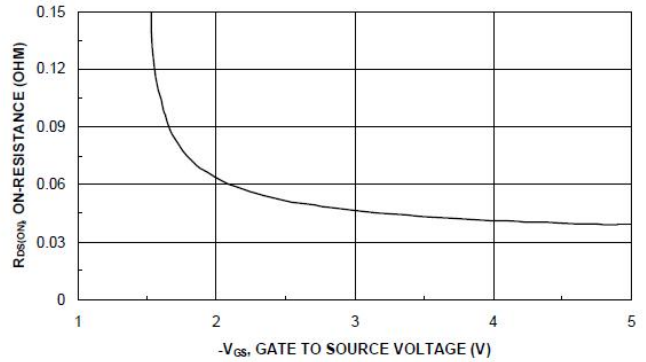


Figure 8. On-Resistance with Gate to Source Voltage

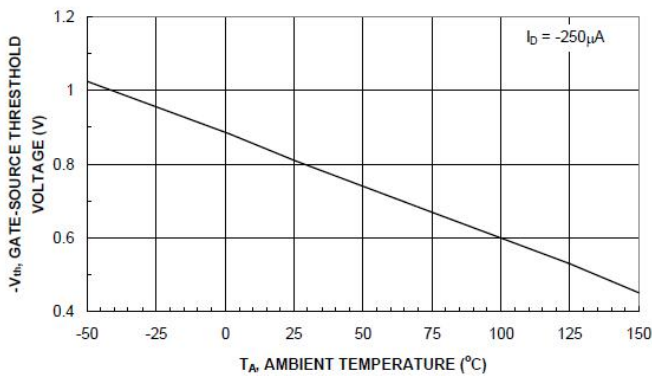


Figure 9. Vth Gate to Source Voltage Vs Temperature

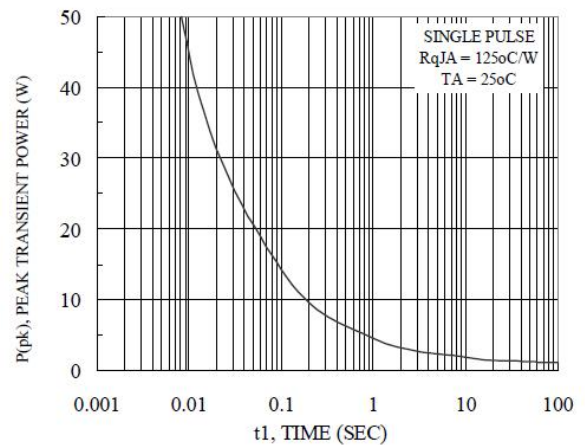


Figure 10. Single Pulse Maximum Power Dissipation

Normalized Thermal Transient Junction to Ambient

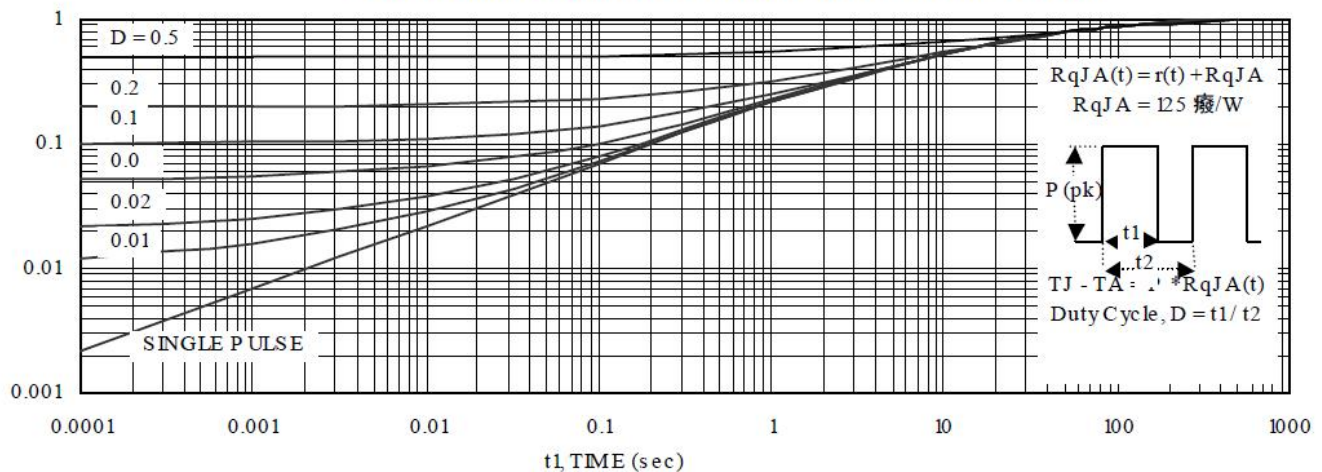


Figure 11. Transient Thermal Response Curve